



#### **DMG8880LSS-13 Information**



For Reference Only

Part Number DMG8880LSS-13
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description**MOSFET N-CH 30V 11.6A 8SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **DMG8880LSS-13 Specifications**

Manufacturer Part Number         DMG8880LSS-13           Manufacturer         Diodes Incorporated           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-SOIC (0.154", 3.90mm Width)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         11.6A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         27.6nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1289pF @ 15V           Vgs (Max)         2V @ 250µA           FET Feature         -           Power Dissipation (Max)         1.43W (Ta)           Rds On (Max) @ Id, Vgs         10 mOhm @ 11.6A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-SOP           Package / Case         8-SOIC (0.154", 3.90mm Width)		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-SOIC (0.154", 3.90mm Width)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         11.6A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         27.6nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1289pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.43W (Ta)           Rds On (Max) @ Id, Vgs         10 mOhm @ 11.6A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-SOP           Package / Case         8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	DMG8880LSS-13
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Package8-SOIC (0.154", 3.90mm Width)Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs27.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1289pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 11.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPPackage / Case8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         11.6A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         27.6nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1289pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.43W (Ta)           Rds On (Max) @ Id, Vgs         10 mOhm @ 11.6A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-SOP           Package / Case         8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  11.6A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 mOhm @ 11.6A, 10V  Operating Temperature  Supplier Device Package  Package / Case  N-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  30V  1.6A (Ta)  1.6A (Ta)  2V @ 250µA  27.6nC @ 10V  1289pF @ 15V  220V  FET Feature  - Continuous Drain (Id) @ 25°C  1.43W (Ta)  1.43W (Ta)  Surface Mount  Supplier Device Package  8-SOP  8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs27.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1289pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 11.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	-
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Ygs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 mOhm @ 11.6A, 10V  Operating Temperature  Supplier Device Package  Package / Case  11.6A (Ta)  1.6A (Ta)  1.	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs27.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1289pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 11.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id       2V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       27.6nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1289pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       1.43W (Ta)         Rds On (Max) @ Id, Vgs       10 mOhm @ 11.6A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       8-SOP         Package / Case       8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	11.6A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1289pF @ 15V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 mOhm @ 11.6A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 mOhm @ 11.6A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.43W (Ta)Rds On (Max) @ Id, Vgs10 mOhm @ 11.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	27.6nC @ 10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 mOhm @ 11.6A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-SOP  Package / Case  8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs10 mOhm @ 11.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-SOP  Package / Case  8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	1.43W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SOP Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	10 mOhm @ 11.6A, 10V
Supplier Device Package 8-SOP Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SOP
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

#### **DMG8880LSS-13 Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **DMG8880LSS-13 Payment Methods**



















### **DMG8880LSS-13 Shipping Methods**













If you have any question about DMG8880LSS-13, please do not hesitate to contact us!

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